PCN Number: 201		161215002		PCN Date:		:	Dec 16, 2016			
Title: Qualification of RFA			AB as additional Fab site option for select LBC8 devices							
Customer Contact:			PCN Manager		Dept:			Quality Services		
Proposed 1 st Ship Date:			Mar 16, 2017 Estimated Availabilit			ted Sample ility:		Date provided at sample request.		
Change Type:										
Assembly Site			Assembly Process					Assembly Materials		
Design		☐ Electrical Specification				Me	chanical Specification			
Test Site				Packing/Shipping/Labeling				Test Process		
Wafer Bump Site			Wafer Bump Material					Wafer Bump Process		
			☐ Wafer Fab Materials				Wa	fer Fab Process		
				Part number change						
	PCN Details									

Description of Change:

Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab source for the selected devices listed in "Product Affected" section.

С	urrent Fab Site	9	Additional Fab Site			
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter	
DP1DM5	LBC8	200 mm	RFAB	LBC8	300 mm	

Qual details are provided in the Qual Data Section.

Reason for Change:

Continuity of Supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

Current:

Current Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DP1DM5	DM5	USA	Dallas

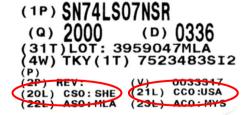
New Fab Site:

New Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
RFAB	RFB	USA	Richardson

Sample product shipping label (not actual product label)







Product Affected:

DRV5013AGQDBZR	DRV5013BCQDBZT	DRV5053OAQDBZR	DRV5053PAQDBZT
DRV5013AGQDBZT	DRV5033AJQDBZR	DRV5053OAQDBZT	DRV5053VAQDBZR
DRV5013BCQDBZR	DRV5033AJQDBZT	DRV5053PAQDBZR	DRV5053VAQDBZT

Qualification Report

DMOS5 offload to RFAB Hall Sensor devices (3 chips) Approved 12/14/2016

Product Attributes

Attributes	Qual Device: DRV5013AGQDBZR	Qual Device: DRV5033AJQDBZR	Qual Device: DRV5053OAQDBZR	QBS Product Reference: C5013ADA1	QBS Product Reference: DRV5013ADEDBZRQ1	QBS Process Reference: SN96019PFP
Assembly Site	HNT	HNT	HNT	HNT	HANA (HNT)	PHI (TIPI)
Package Family	SOT	SOT	SOT	SOT	SOT	HTQFP
Wafer Fab Supplier	RFAB	RFAB	RFAB	RFAB	DFAB/DMOS5	RFAB
Wafer Process	LBC8	LBC8	LBC8	LBC8	LBC8	LBC8
QBS: Qual By Similarity						
- Qual Devices qualified at LEVEL1-260C: DRV5013AGQDBZR, DRV5053OAQDBZR, DRV5033AJQDBZR						
Qualification Results						

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: DRV5013AGQDBZR	Qual Device: DRV5033AJQDBZR	Qual Device: DRV5053OAQDBZR	QBS Product Reference: C5013ADA1	QBS Product Reference: DRV5013ADEDBZRQ1	QBS Process Reference: SN96019PFP
AC	Autoclave 121C	96 Hours		-	-	3/231/0	3/231/0	3/231/0
ED	Auto Electrical Distributions	Cpk>1.33, Ppk>1.67 Room, hot, and cold test	-	-	-	-	1/30/0	-
ED	Electrical Characterization	Per Datasheet Parameters	Conditional	Conditional	Conditional	1/30/0	-	1/30/0
ELFR	Early Life Failure Rate, 150C	48 Hours	-	-	-	-	3/2400/0	-
HAST	Biased HAST, 130C/85%RH	96 Hours		-	-	3/231/0	3/231/0	3/231/0
HBM	ESD - HBM	2500 V	-	-	-	-	1/3/0	-
CDM	ESD - CDM	1000 V		-	-	-	1/3/0	-
HTOL	Life Test, 125C	1000 Hours	-	-	-	-	-	3/231/0
HTOL	Life Test, 150C	1000 Hours	-	-	-	1/77/0	3/231/0	-
HTSL	High Temp. Storage Bake, 170C	420 Hours		-	-	-	-	3/231/0
HTSL	High Temp. Storage Bake, 175C	500 Hours		-	-	-	1/47/0	-
LU	Latch-up	(per JESD78)	-	-	-	-	2/12/0	1/6/0
SD	Surface Mount Solderability	Pb Free	-	-	-	-	1/15/0	-
TC	Temperature Cycle, -65/150C	500 Cycles	-	-	-	3/231/0	3/231/0	3/231/0
WBP	Bond Pull	Wires		-	-	-	1/5/0	-

⁻ Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

Green/Pb-free Status: Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com

⁻ The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent HTSL options part ESD47 - 55C/125C/700 Cycles and -65C/150C/500 Cycles
- Quality and Environmental data is available at TI's external Web site: http://www.ti.com/